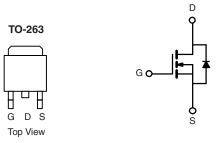


www.vishay.com

Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.015			
I _D (A)	56			
Configuration	Single			



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- 100 % R_a and UIS Tested
- Characterization Ongoing
- Compliant to RoHS Directive 2002/95/EC



RoHS COMPLIANT
HALOGEN FREE

ORDERING INFORMATION			
Package	TO-263		
Lead (Pb)-free and Halogen-free	SQM60N06-15-GE3		

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C	I _D	56		
Continuous Drain Current	T _C = 125 °C		32		
Continuous Source Current (Diode Conduction) ^a	I _S	60	Α		
Pulsed Drain Current ^b	I _{DM}	227			
Single Pulse Avalanche Current L = 0.1 mH		I _{AS}	29		
Single Pulse Avalanche Energy	L=0.11IIII	E _{AS}	42	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	107	W	
waxiiiuiii rowei Dissipatioli~	T _C = 125 °C	P_D	35	VV	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient P	PCB Mount ^c	R_{thJA}	40	°C/W	
Junction-to-Case (Drain)		R_{thJC}	1.4	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		60	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	2.5	-	3.5]	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 60 V	-	-	1.0		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	75	-	-	Α	
		V _{GS} = 10 V	I _D = 30 A	-	0.012	0.015	0.015 0.027 Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.027		
	, ,	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.033		
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 30 A		-	61	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	1983	2480		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = 25 V, f = 1 MHz		314	395	pF	
Reverse Transfer Capacitance	C _{rss}			-	125	160		
Total Gate Charge ^c	Qg			-	33	50		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 60 \text{ A}$	-	8.9	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	7.4	-		
Gate Resistance	R _g		f = 1 MHz		1.6	2.4	Ω	
Turn-On Delay Time ^c	t _{d(on)}				11	17		
Rise Time ^c	t _r	$V_{DD}=30$ V, $R_L=0.5$ Ω $I_D\cong 60$ A, $V_{GEN}=10$ V, $R_g=1$ Ω		-	12	18	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	21	32		
Fall Time ^c	t _f			-	7	11		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	227	Α	
Forward Voltage	V _{SD}	I _F = 30 A, V _{GS} = 0		-	0.9	1.5	V	

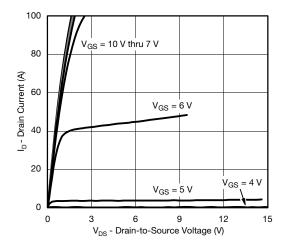
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

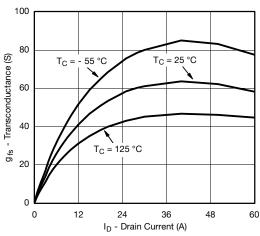
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



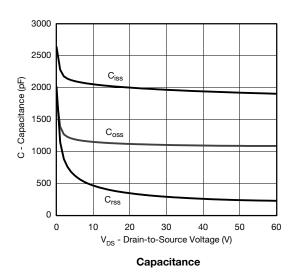
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

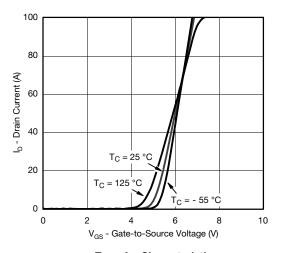


Output Characteristics

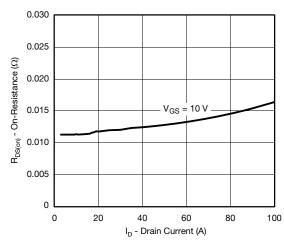


Transconductance

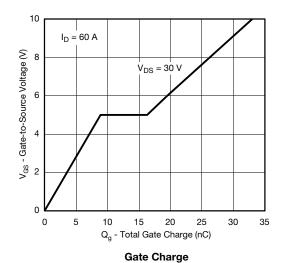




Transfer Characteristics

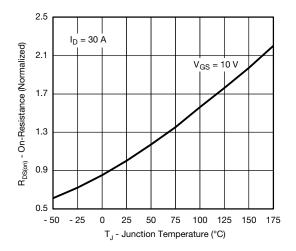


On-Resistance vs. Drain Current

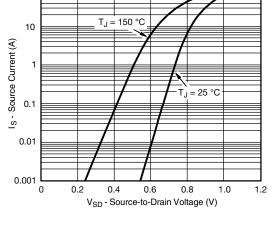




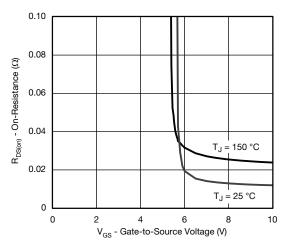
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



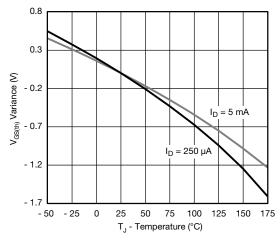
On-Resistance vs. Junction Temperature



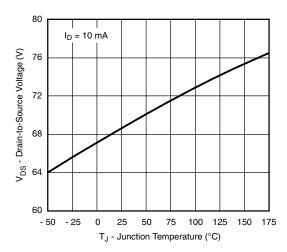
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



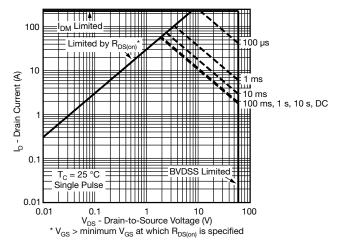
Threshold Voltage



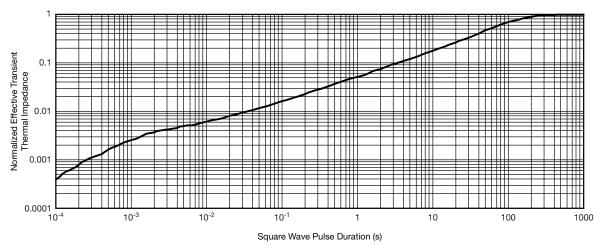
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)

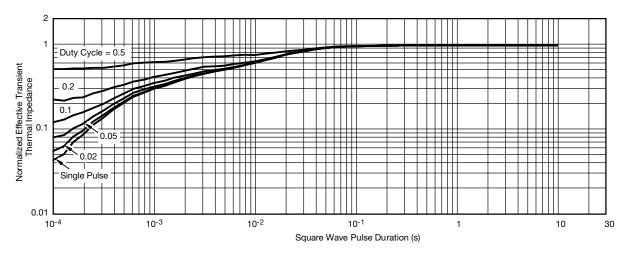


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

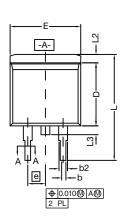
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

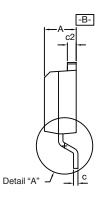
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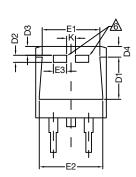




TO-263 (D²PAK): 3-LEAD

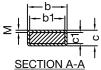








DETAIL A (ROTATED 90°)



_	ļ	—b— b1		
2	T		5	
	٥ ا	CTION	Λ- <i>i</i>	(†

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

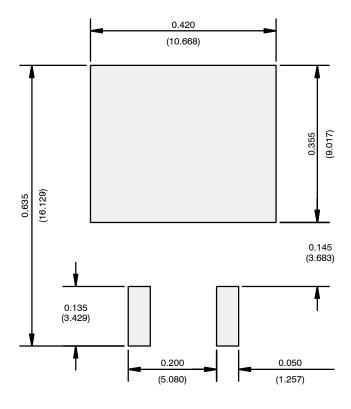
		INC	HES	MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
	Α	0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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Revision: 02-Oct-12 Document Number: 91000